

# PSMN2R5-30YL

# N-channel 30 V 2.4 mΩ logic level MOSFET in LFPAK Rev. 04 — 10 March 2011 Product

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

# 1.3 Applications

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol               | Parameter  | Conditions  |            | Min | Тур  | Max | Unit |
|----------------------|--|---|------------|-----|------|-----|------|
| $V_{DS}$             | drain-source voltage                               | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$   |            | -   | -    | 30  | V    |
| I <sub>D</sub>       | drain current                                      | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>  | <u>[1]</u> | -   | -    | 100 | Α    |
| P <sub>tot</sub>     | total power dissipation                            | T <sub>mb</sub> = 25 °C; see Figure 2   |            | -   | -    | 88  | W    |
| T <sub>j</sub>       | junction temperature                               |   |            | -55 | -    | 175 | °C   |
| Static chara         | acteristics  |   |            |     |      |     |      |
| R <sub>DSon</sub>    | drain-source on-state resistance                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$<br>$T_j = 25 \text{ °C}$   |            | -   | 1.79 | 2.4 | mΩ   |
| Dynamic ch           | naracteristics                                     |   |            |     |      |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$   |            | -   | 6.5  | -   | nC   |
| Q <sub>G(tot)</sub>  | total gate charge                                  | V <sub>DS</sub> = 12 V; see <u>Figure 14;</u><br>see <u>Figure 15</u>   |            | -   | 27   | -   | nC   |
| Avalanche ruggedness |  |   |            |     |      |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C;<br>$I_D$ = 100 A; $V_{sup} \le$ 30 V;<br>$R_{GS}$ = 50 $\Omega$ ; unclamped |            | -   | -    | 103 | mJ   |

<sup>[1]</sup> Continuous current is limited by package.



# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | S      | source                            |                    |                |
| 2   | S      | source                            | mb (               | D              |
| 3   | S      | source                            |                    |                |
| 4   | G      | gate                              |                    |                |
| mb  | D      | mounting base; connected to drain | 1 2 3 4            | mbb076 S       |
|     |        |                                   | SOT669 (LFPAK)     |                |

# 3. Ordering information

Table 3. Ordering information

| Type number  | Package |   |         |
|--------------|---------|---|---------|
|              | Name    | Description   | Version |
| PSMN2R5-30YL | LFPAK   | plastic single-ended surface-mounted package (LFPAK); 4 leads | SOT669  |

# 4. Limiting values

Table 4. Limiting values

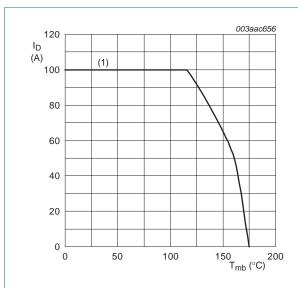
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions  | Min          | Max | Unit |  |  |
|----------------------|--|---|--------------|-----|------|--|--|
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   | -            | 30  | V    |  |  |
| $V_{DSM}$            | peak drain-source voltage                    | $t_p \le 25 \text{ ns; } f \le 500 \text{ kHz;}$<br>$E_{DS(AL)} \le 240 \text{ nJ; pulsed}$                 | -            | 35  | V    |  |  |
| $V_{DGR}$            | drain-gate voltage                           | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$                                | -            | 30  | V    |  |  |
| $V_{GS}$             | gate-source voltage                          |   | -20          | 20  | V    |  |  |
| $I_D$                | drain current                                | $V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$         | <u>[1]</u> _ | 100 | Α    |  |  |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>  | <u>[1]</u> _ | 100 | Α    |  |  |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3  | -            | 580 | Α    |  |  |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  | -            | 88  | W    |  |  |
| T <sub>stg</sub>     | storage temperature                          |   | -55          | 175 | °C   |  |  |
| Tj                   | junction temperature                         |   | -55          | 175 | °C   |  |  |
| Source-drain         | diode  |   |              |     |      |  |  |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C   | <u>[1]</u> - | 100 | Α    |  |  |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$  | -            | 580 | Α    |  |  |
| Avalanche ru         | Avalanche ruggedness                         |   |              |     |      |  |  |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped | -            | 103 | mJ   |  |  |

<sup>[1]</sup> Continuous current is limited by package.

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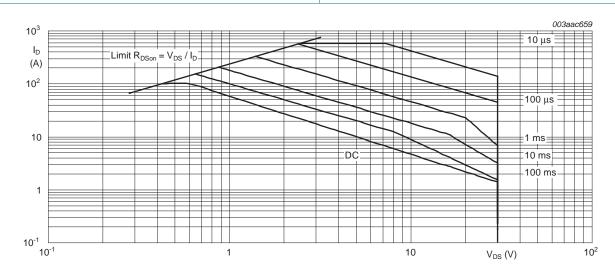
 $V_{GS} \ge 10 \text{ V}$ ; (1) Capped at 100 A due to package.

120 P<sub>der</sub> (%) 80 40 0 150 T<sub>mb</sub> (°C)

 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

Continuous drain current as a function of mounting base temperature

Normalized total power dissipation as a function of mounting base temperature



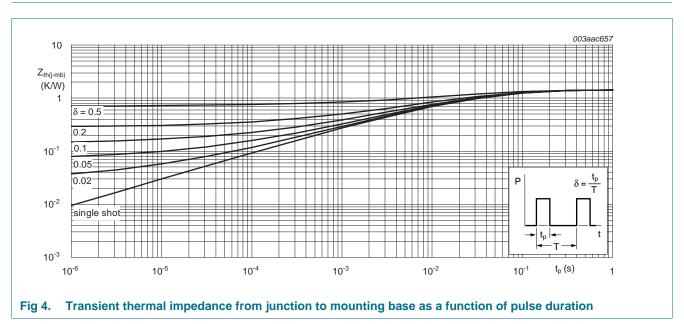
 $V_{GS} \ge 10\,V$ (1) Capped at 100 A due to package.

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

# 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions   | Min | Тур | Max | Unit |
|----------------|---|--------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | -   | -   | 1.4 | K/W  |



# 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

| Symbol                 | Parameter                            | Conditions   | Min  | Тур  | Max  | Unit             |
|------------------------|--------------------------------------|--|------|------|------|------------------|
| Static chara           | cteristics                           |  |      |      |      |                  |
| $V_{(BR)DSS}$          | drain-source                         | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$   | 30   | -    | -    | V                |
|                        | breakdown voltage                    | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$   | 27   | -    | -    | V                |
| ()                     | gate-source threshold voltage        | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C;<br>see <u>Figure 11</u> ; see <u>Figure 12</u>                        | 1.3  | 1.7  | 2.15 | V                |
|                        |                                      | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see <u>Figure 12</u>   | 0.65 | -    | -    | V                |
|                        |                                      | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C;<br>see <u>Figure 12</u>  | -    | -    | 2.45 | V                |
| I <sub>DSS</sub>       | drain leakage current                | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -    | -    | 1    | μΑ               |
|                        |                                      | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$  | -    | -    | 100  | μΑ               |
| $I_{GSS}$              | gate leakage current                 | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -    | -    | 100  | nA               |
|                        |                                      | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | -    | -    | 100  | nA               |
| Doon                   | drain-source on-state                | $V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$  | -    | 2.47 | 3.16 | $\text{m}\Omega$ |
|                        | resistance                           | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 13                                 | -    | -    | 4.2  | mΩ               |
|                        |                                      | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$   | -    | 1.79 | 2.4  | $m\Omega$        |
| R <sub>G</sub>         | gate resistance                      | f = 1 MHz  | -    | 0.67 | 1.5  | Ω                |
| Dynamic ch             | aracteristics                        |  |      |      |      |                  |
| Q <sub>G(tot)</sub>    | total gate charge                    | $I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14; see Figure 15               | -    | 27   | -    | nC               |
|                        |                                      | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$   | -    | 52   | -    | nC               |
|                        |                                      | $I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u> | -    | 57   | -    | nC               |
| $Q_{GS}$               | gate-source charge                   | $I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;  | -    | 8.5  | -    | nC               |
| Q <sub>GS(th)</sub>    | pre-threshold<br>gate-source charge  | see <u>Figure 14;</u> see <u>Figure 15</u>   | -    | 5.7  | -    | nC               |
| Q <sub>GS(th-pl)</sub> | post-threshold<br>gate-source charge |  | -    | 2.8  | -    | nC               |
| $Q_{GD}$               | gate-drain charge                    |  | -    | 6.5  | -    | nC               |
| V <sub>GS(pl)</sub>    | gate-source plateau<br>voltage       | V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ;<br>see <u>Figure 15</u>   | -    | 2.35 | -    | V                |
| C <sub>iss</sub>       | input capacitance                    | V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;  | -    | 3468 | -    | pF               |
| C <sub>oss</sub>       | output capacitance                   | T <sub>j</sub> = 25 °C; see <u>Figure 16</u>   | -    | 710  | -    | pF               |
| C <sub>rss</sub>       | reverse transfer capacitance         |  | -    | 314  | -    | pF               |
| t <sub>d(on)</sub>     | turn-on delay time                   | $V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$   | -    | 39   | -    | ns               |
| t <sub>r</sub>         | rise time                            | $R_{G(ext)} = 4.7 \Omega$  | -    | 62   | -    | ns               |
| t <sub>d(off)</sub>    | turn-off delay time                  |  | -    | 61   | -    | ns               |
| t <sub>f</sub>         | fall time                            |  | -    | 25   | -    | ns               |
|                        |                                      |  |      |      |      |                  |

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 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

| Symbol          | Parameter             | Conditions   | Min | Тур  | Max | Unit |
|-----------------|-----------------------|--|-----|------|-----|------|
| Source-drain    | n diode               |  |     |      |     |      |
| V <sub>SD</sub> | source-drain voltage  | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$<br>see <u>Figure 17</u> | -   | 0.79 | 1.2 | V    |
| t <sub>rr</sub> | reverse recovery time | $I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;       | -   | 39   | -   | ns   |
| $Q_r$           | recovered charge      | $V_{DS} = 20 \text{ V}$  | -   | 38   | -   | nC   |

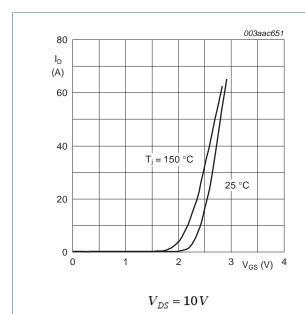
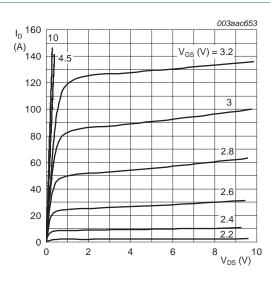


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

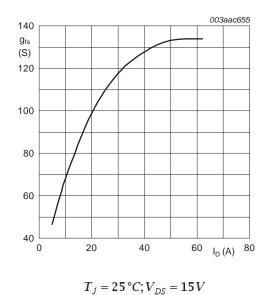
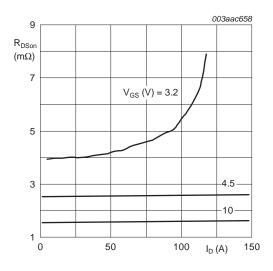


Fig 7. Forward transconductance as a function of drain current; typical values



 $T_j = 25 \,^{\circ}C; t_p = 300 \mu s$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values

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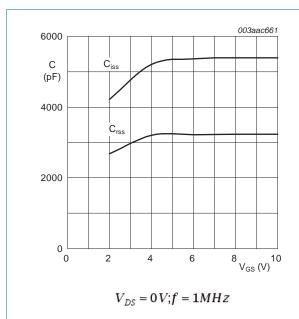


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

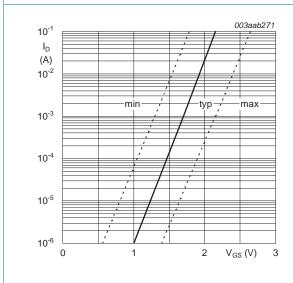
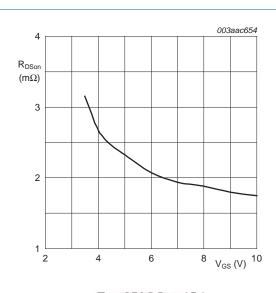


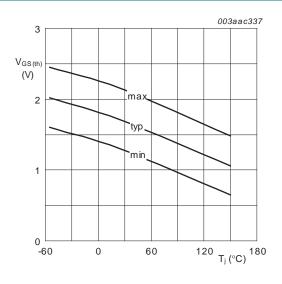
Fig 11. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 



 $T_j=25\,^{\circ}C; I_D=15A$ 

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$ 

Fig 12. Gate-source threshold voltage as a function of junction temperature

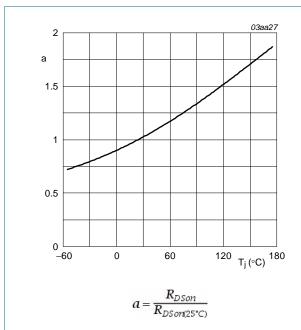


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

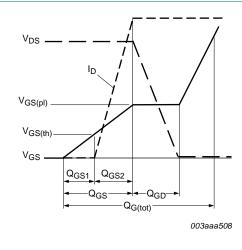


Fig 14. Gate charge waveform definitions

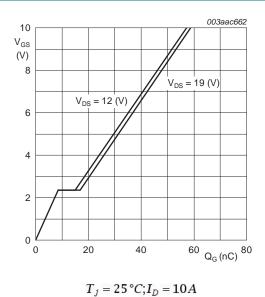
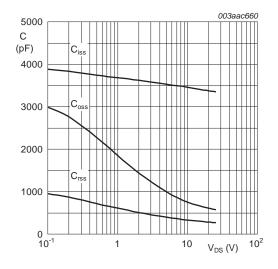


Fig 15. Gate-source voltage as a function of gate

charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

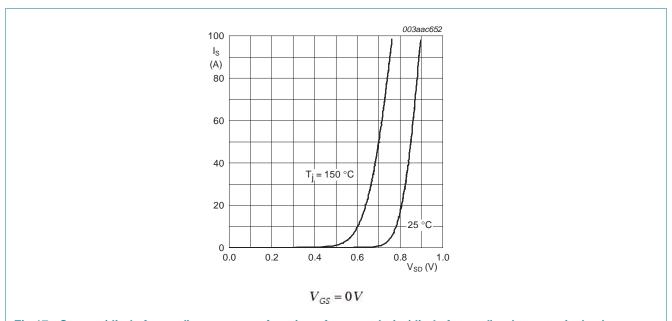


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline

#### Plastic single-ended surface-mounted package (LFPAK); 4 leads **SOT669** С c<sub>2</sub> - $E_1$ mounting $b_4$ base $D_1$ D **→** w M A 1/2 e $(A_3)$ С detail X 5 mm scale **DIMENSIONS (mm are the original dimensions)** D<sub>1</sub><sup>(1)</sup> $A_2$ $b_3$ E<sup>(1)</sup> UNIT Α b $b_2$ $b_4$ $D^{(1)}$ E<sub>1</sub><sup>(1)</sup> $L_2$ θ Α<sub>1</sub> A<sub>3</sub> С $c_2$ е $L_1$ у 1.20 0.15 1.10 0.50 4.41 0.9 0.25 0.30 4.10 3.3 6.2 0.85 1.3 0.25 0.00 0.95 0.35 3.62 2.0 0.7 0.19 0.24 3.80 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included. REFERENCES **EUROPEAN** OUTLINE **ISSUE DATE PROJECTION** VERSION IEC JEDEC JEITA

Fig 18. Package outline SOT669 (LFPAK)

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04-10-13

06-03-16

SOT669

# 8. Revision history

### Table 7. Revision history

| Document ID      | Release date                        | Data sheet status  | Change notice | Supersedes       |
|------------------|-------------------------------------|--------------------|---------------|------------------|
| PSMN2R5-30YL v.4 | 20110310                            | Product data sheet | -             | PSMN2R5-30YL v.3 |
| Modifications:   | <ul> <li>Various changes</li> </ul> | to content.        |               |                  |
| PSMN2R5-30YL v.3 | 20091228                            | Product data sheet | -             | PSMN2R5-30YL v.2 |

# 9. Legal information

### 9.1 Data sheet status

| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions'
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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### N-channel 30 V 2.4 m $\Omega$ logic level MOSFET in LFPAK

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## 10. Contact information

For more information, please visit: http://www.nexperia.com

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# PSMN2R5-30YL

# **Nexperia**

N-channel 30 V 2.4 mΩ logic level MOSFET in LFPAK

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